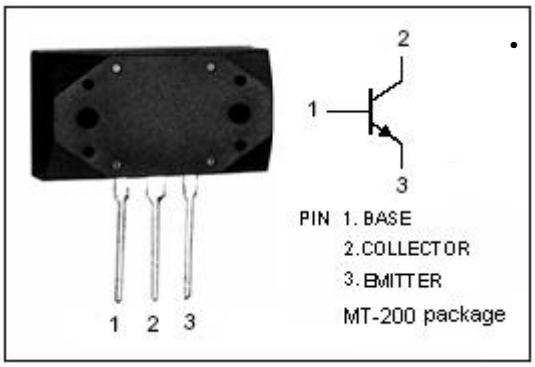
isc Silicon NPN Power Transistor — 2SC2793



DESCRIPTION

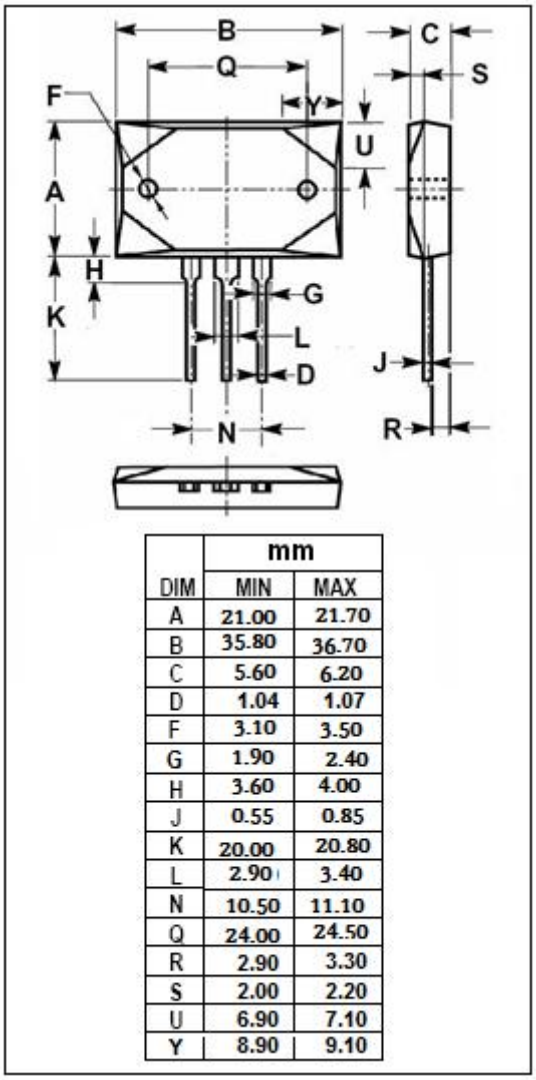
- With MT-200 package
- High power dissipation
- High current capability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.

APPLICATIONS

- High speed and high voltage switching applications
- Switching regulator applications
- High speed DC-DC converter applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	900	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	5	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation @ T_C=25℃	100	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	21.00	21.70
B	35.80	36.70
C	5.60	6.20
D	1.04	1.07
F	3.10	3.50
G	1.90	2.40
H	3.60	4.00
J	0.55	0.85
K	20.00	20.80
L	2.90	3.40
N	10.50	11.10
Q	24.00	24.50
R	2.90	3.30
S	2.00	2.20
U	6.90	7.10
Y	8.90	9.10

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ; I_B=0	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3A; I_B=0.6A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3A; I_B=0.6A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=900V; I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			100	μA
h_{FE-1}	DC current gain	I_C=10mA ; V_{CE}=5V	10			
h_{FE-2}	DC current gain	I_C=3A ; V_{CE}=5V	10			